



Substitute for Form 1449/APTO				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				Application Number	10/676,969
				Filing Date	09/30/2003
				First Named Inventor	Gupta, et al.
				Group Art Unit	2814
				Examiner Name	Ngo, Ngan V.
Sheet	1	of	1	Attorney Docket Number	2003P12642US

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
W		6,274,979		Celi et al.	—	—
W		6,580,213		Yamazaki	—	—
W		6,588,764		Buechel et al.	—	—

OTHER NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		
W	A	S.M. Sze, "Physics of Semiconductor Devices", 2 <sup>nd</sup> Edition, 1981, Pgs. 270-273 and 516-531		
W	B	"Voltage Reduction in Organic Light-Emitting Diodes", L.S. Hung, M.G. Mason, Applied Physics Letters, Volume 78, Number 23, June 2, 2001, Pgs. 3732-3734		
W	C	"Enhanced Hole Injection in a Bilayer Vacuum-Deposited Organic Light-Emitting Device Using a P-Type Doped Silicon Anode", X. Zhou, J. He, L. S. Liao, M. Lu, Z. H. Xiong, X.M. Ding, X. Y. Hou, F.G. Tao, C.E. Zhou and S.T. Lee, Applied Physics Letters, Volume 74, Number 4, January 25, 1999, Pgs. 609-611		

Examiner Signature	<i>M/m</i>	Date Considered	3-18-05
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. (Include copy of this form with next communication to applicant.)

<sup>1</sup>Unique citation designation number. <sup>2</sup>See attached Kinds of U.S. Patent Documents. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.